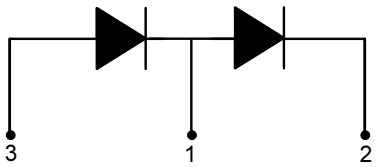
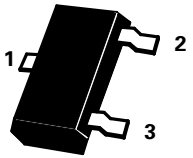
SOT23 SILICON PLANAR LOW LEAKAGE SERIES DIODE PAIR

FLLD261

ISSUE 2 – SEPTEMBER 1995 ✪

DIODE PIN CONNECTION





SOT23

PART MARKING DETAIL – P8A

ABSOLUTE MAXIMUM RATINGS.

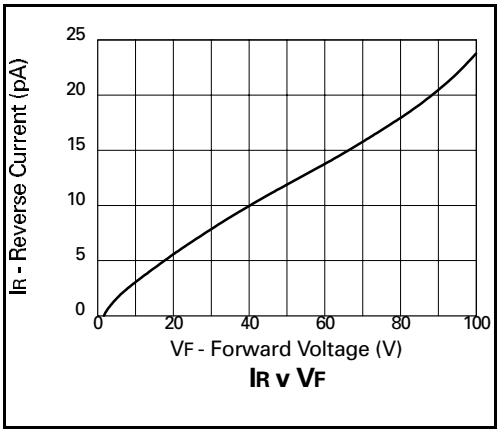
PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current (t=1μs)	I_{FSM}	3.0	A
Power Dissipation at T_{amb} = 25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	I_R		5 5	nA μA	V_{RRM}=100V V_{RRM}=100V, T_{amb}=150°C
Reverse Recovery Time*	t_{rr}		400	ns	I_F= I_R=50 – 400mA
Forward Recovery Time	t_{fr}		10	ns	I_F=10mA
Diode Capacitance	C_d		4	pF	V_R=1V, f=1MHz
Forward Overshoot Voltage	V_{fr}		Typ 0.9	V	I_F=10mA, Rise time=5ns ±20%
Forward Voltage	V_F		1.4	V	I_F=-200mA

*Time for I_R to recover to 10% of I_R peak
For typical characteristics graphs see FLLD263 datasheet.

TYPICAL CHARACTERISTICS



IR v VF